HARRIS SEMICONDUCTOR

CD74HC253, CD74HCT253

High Speed CMOS Logic Dual 4-Input Multiplexer

November 1997

Features

- Common Select Inputs
- Separate Output-Enable Inputs
- Three-State Outputs
- Fanout (Over Temperature Range)
  - Standard Outputs . . . . . 10 LSTTL Loads
  - Bus Driver Outputs . . . . . 15 LSTTL Loads
- Wide Operating Temperature Range . . . -55°C to 125°C
- Balanced Propagation Delay and Transition Times
- Significant Power Reduction Compared to LSTTL Logic ICs
- HC Types
  - 2V to 6V Operation
  - High Noise Immunity: N_{IL} = 30%, N_{IH} = 30% of V_{CC} at V_{CC} = 5V
- HCT Types
  - 4.5V to 5.5V Operation
  - Direct LSTTL Input Logic Compatibility, V_{IL}= 0.8V (Max), V_{IH} = 2V (Min)
  - CMOS Input Compatibility, $I_I \leq 1\mu A$ at V_{OL}, V_{OH}

Description

The Harris CD74HC253 and CD74HCT253 are dual 4-to-1 line selector/multiplexers having three-state outputs. One of four sources for each section is selected by the common select inputs, S0 and S1. When the output enable ($\overline{1OE}$, $\overline{2OE}$) is HIGH, the output is in the high-impedance state.

Ordering Information

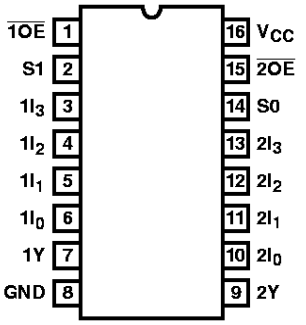
PART NUMBER	TEMP. RANGE (°C)	PACKAGE	PKG. NO.
CD74HC253E	-55 to 125	16 Ld PDIP	E16.3
CD74HCT253E	-55 to 125	16 Ld PDIP	E16.3
CD74HC253M	-55 to 125	16 Ld SOIC	M16.15
CD74HCT253M	-55 to 125	16 Ld SOIC	M16.15

NOTES:

1. When ordering, use the entire part number. Add the suffix 96 to obtain the variant in the tape and reel.
2. Wafer or die for this part number is available which meets all electrical specifications. Please contact your local sales office or Harris customer service for ordering information.

Pinout

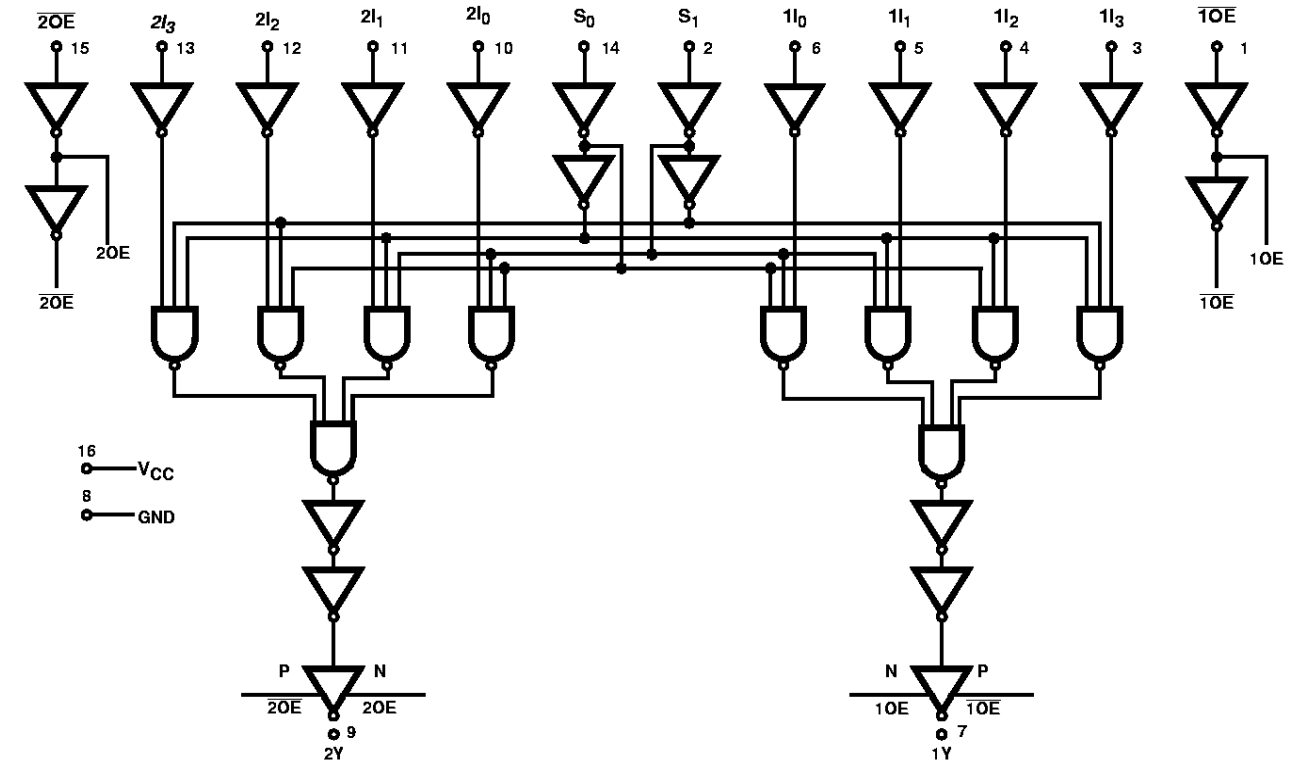
CD74HC253, CD74HCT253
(PDIP, SOIC)
TOP VIEW



CAUTION: These devices are sensitive to electrostatic discharge. Users should follow proper IC Handling Procedures.

File Number **1673.1**

Functional DiagramS



TRUTH TABLE

SELECT INPUTS		DATA INPUTS				OUTPUT ENABLE	OUTPUT
S1	S0	I_0	I_1	I_2	I_3	$\overline{OE}$	Y
X	X	X	X	X	X	H	Z
L	L	L	X	X	X	L	L
L	L	H	X	X	X	L	H
L	H	X	L	X	X	L	L
L	H	X	H	X	X	L	H
H	L	X	X	L	X	L	L
H	L	X	X	H	X	L	H
H	H	X	X	X	L	L	L
H	H	X	X	X	H	L	H

NOTE:
Select inputs S1 and S0 are common to both sections.
H = High Voltage Level, L = Low Voltage Level, X = Don't Care, Z = High Impedance (Off).

Absolute Maximum Ratings

DC Supply Voltage, V_{CC} . . . . . -0.5V to 7V
DC Input Diode Current, I_{IK}
For V_I < -0.5V or V_I > V_{CC} + 0.5V . . . . . ±20mA
DC Output Diode Current, I_{OK}
For V_O < -0.5V or V_O > V_{CC} + 0.5V . . . . . ±20mA
DC Drain Current, per Output, I_O
For -0.5V < V_O < V_{CC} + 0.5V. . . . . ±35mA
DC Output Source or Sink Current per Output Pin, I_O
For V_O > -0.5V or V_O < V_{CC} + 0.5V . . . . . ±25mA
DC V_{CC} or Ground Current, I_{CC} . . . . . ±50mA

Operating Conditions

Temperature Range, T_A . . . . . -55°C to 125°C
Supply Voltage Range, V_{CC}
HC Types . . . . . 2V to 6V
HCT Types . . . . . 4.5V to 5.5V
DC Input or Output Voltage, V_I, V_O . . . . . 0V to V_{CC}
Input Rise and Fall Time
2V . . . . . 1000ns (Max)
4.5V. . . . . 500ns (Max)
6V . . . . . 400ns (Max)

Thermal Information

Thermal Resistance (Typical, Note 3) θ_{JA} (°C/W)
PDIP Package 90
SOIC Package 160
Maximum Junction Temperature . . . . . 150°C
Maximum Storage Temperature Range . . . . . -65°C to 150°C
Maximum Lead Temperature (Soldering 10s) . . . . . 300°C
(SOIC - Lead Tips Only)

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

NOTE:

3. θ_{JA} is measured with the component mounted on an evaluation PC board in free air.

DC Electrical Specifications

PARAMETER	SYMBOL	TEST CONDITIONS		V_{CC} (V)	25°C			-40°C TO 85°C		-55°C TO 125°C		UNITS
		V_I (V)	I_O (mA)		MIN	TYP	MAX	MIN	MAX	MIN	MAX	
HC TYPES												
High Level Input Voltage	V_{IH}	-	-	2	1.5	-	-	1.5	-	1.5	-	V
				4.5	3.15	-	-	3.15	-	3.15	-	V
				6	4.2	-	-	4.2	-	4.2	-	V
Low Level Input Voltage	V_{IL}	-	-	2	-	-	0.5	-	0.5	-	0.5	V
				4.5	-	-	1.35	-	1.35	-	1.35	V
				6	-	-	1.8	-	1.8	-	1.8	V
High Level Output Voltage CMOS Loads	V_{OH}	V_{IH} or V_{IL}	-0.02	2	1.9	-	-	1.9	-	1.9	-	V
			-0.02	4.5	4.4	-	-	4.4	-	4.4	-	V
			-0.02	6	5.9	-	-	5.9	-	5.9	-	V
High Level Output Voltage TTL Loads			-	-	-	-	-	-	-	-	-	V
			-6	4.5	3.98	-	-	3.84	-	3.7	-	V
			-7.8	6	5.48	-	-	5.34	-	5.2	-	V
Low Level Output Voltage CMOS Loads	V_{OL}	V_{IH} or V_{IL}	0.02	2	-	-	0.1	-	0.1	-	0.1	V
			0.02	4.5	-	-	0.1	-	0.1	-	0.1	V
			0.02	6	-	-	0.1	-	0.1	-	0.1	V
Low Level Output Voltage TTL Loads			-	-	-	-	-	-	-	-	-	V
			-6	4.5	-	-	0.26	-	0.33	-	0.4	V
			-7.8	6	-	-	0.26	-	0.33	-	0.4	V
Input Leakage Current	I_I	V_{CC} or GND	-	6	-	-	±0.1	-	±1	-	±1	µA

DC Electrical Specifications (Continued)

PARAMETER	SYMBOL	TEST CONDITIONS		V_{CC} (V)	25°C			-40°C TO 85°C		-55°C TO 125°C		UNITS
		V_I (V)	I_O (mA)		MIN	TYP	MAX	MIN	MAX	MIN	MAX	
Quiescent Device Current	I_{CC}	V_{CC} or GND	0	6	-	-	8	-	80	-	160	µA
HCT TYPES												
High Level Input Voltage	V_{IH}	-	-	4.5 to 5.5	2	-	-	2	-	2	-	V
Low Level Input Voltage	V_{IL}	-	-	4.5 to 5.5	-	-	0.8	-	0.8	-	0.8	V
High Level Output Voltage CMOS Loads	V_{OH}	V_{IH} or V_{IL}	-0.02	4.5	4.4	-	-	4.4	-	4.4	-	V
High Level Output Voltage TTL Loads			-4	4.5	3.98	-	-	3.84	-	3.7	-	V
Low Level Output Voltage CMOS Loads	V_{OL}	V_{IH} or V_{IL}	0.02	4.5	-	-	0.1	-	0.1	-	0.1	V
Low Level Output Voltage TTL Loads			4	4.5	-	-	0.26	-	0.33	-	0.4	V
Input Leakage Current	I_I	V_{CC} and GND	0	5.5	-	-	±0.1	-	±1	-	±1	µA
Quiescent Device Current	I_{CC}	V_{CC} or GND	0	5.5	-	-	8	-	80	-	160	µA
Additional Quiescent Device Current Per Input Pin: 1 Unit Load	ΔI_{CC} (Note)	V_{CC} -2.1	-	4.5 to 5.5	-	100	360	-	450	-	490	µA
Three-State Leakage Current	I_{OZ}	V_{IL} or V_{IH}	V_O = V_{CC} or GND	5.5	-	-	±0.5	-	±5	-	±10	µA

NOTE: For dual-supply systems theoretical worst case (V_I = 2.4V, V_{CC} = 5.5V) specification is 1.8mA.

HCT Input Loading Table

INPUT	UNIT LOADS
$1I_O$ - $1I_3$, $2I_O$-$2I_3$	0.4
$1E_O$, $2E_O$, S_0, S_1	1

NOTE: Unit Load is ΔI_{CC} limit specified in DC Electrical Table, e.g., 360µA max at 25°C.

Switching Specifications Input t_r, t_f = 6ns

PARAMETER	SYMBOL	TEST CONDITIONS	V_{CC} (V)	25°C			-40°C TO 85°C		-55°C TO 125°C		UNITS
				MIN	TYP	MAX	MIN	MAX	MIN	MAX	
HC TYPES											
Propagation Delay Select to Outputs	t_{PLH}, t_{PHL}	C_L = 50pF	2	-	-	175	-	220	-	265	ns
			4.5	-	-	35	-	44	-	53	ns
		C_L =15pF	5	-	14	-	-	-	-	-	ns
		C_L = 50pF	6	-	-	30	-	37	-	45	ns

Switching Specifications Input t_r, t_f = 6ns **(Continued)**

PARAMETER	SYMBOL	TEST CONDITIONS	V_{CC} (V)	25°C			-40°C TO 85°C		-55°C TO 125°C		UNITS
				MIN	TYP	MAX	MIN	MAX	MIN	MAX	
Data to Outputs	t_{PLH}, t_{PHL}	C_L = 50pF	2	-	-	175	-	220	-	265	ns
			4.5	-	-	35	-	44	-	53	ns
		C_L =15pF	5	-	14	-	-	-	-	-	ns
		C_L = 50pF	6	-	-	30	-	37	-	45	ns
Disable Delay Times	t_{PHZ}, t_{PLZ}	C_L = 50pF	2	-	-	150	-	190	-	225	ns
		C_L = 50pF	4.5	-	-	30	-	38	-	45	ns
		CL = 15pF	5	-	12	-	-	-	-	-	ns
		C_L = 50pF	6	-	-	26	-	33	-	38	ns
Enable Delay Times	t_{PZH}, t_{PZL}	C_L = 50pF	2	-	-	110	-	140	-	165	ns
		CL = 50pF	4.5	-	-	22	-	28	-	33	ns
		CL = 15pF	5	-	9	-	-	-	-	-	ns
		CL = 50pF	6	-	-	19	-	24	-	28	ns
Output Transition Times	t_{TLH}, t_{THL}	C_L = 50pF	2	-	-	60	-	75	-	90	ns
			4.5	-	-	12	-	15	-	18	ns
			6	-	-	10	-	13	-	15	ns
Input Capacitance	C_I	-	-	-	-	10	-	10	-	10	pF
Three-State Output Capacitance	C_O	-	-	-	-	20	-	20	-	20	pF
Power Dissipation Capacitance (Notes 4, 5)	C_{PD}	-	5	-	46	-	-	-	-	-	pF
HCT TYPES											
Propagation Delay Select to Outputs	t_{PLH}, t_{PHL}	C_L = 50pF	4.5	-	-	40	-	50	-	60	ns
		C_L =15pF	5	-	16	-	-		-	-	ns
Data to Outputs	t_{PLH}, t_{PHL}	C_L = 50pF	4.5	-	-	38	-	48	-	57	ns
		C_L =15pF	5	-	16	-	-	-	-	-	ns
Disable Delay Times	t_{PLH}, t_{PHL}	C_L = 50pF	4.5	-		30	-	38	-	45	ns
		C_L =15pF	5	-	12	-	-	-	-	-	ns
Enable Delay Times	t_{PZH}, t_{PZL}	C_L = 50pF	4.5	-	-	30	-	38	-	45	ns
		C_L =15pF	5	-	12	-	-	-	-	-	ns
Output Transition Time	t_{TLH}, t_{THL}	C_L = 50pF	4.5	-	-	12	-	15	-	18	ns
Input Capacitance	C_{IN}	-	-	-	-	10	-	10	-	10	pF
Three-State Output Capacitance	C_O	-	-	-	-	20	-	20	-	20	pF
Power Dissipation Capacitance (Notes 4, 5)	C_{PD}	-	5	-	52	-	-	-	-	-	pF

NOTES:

4. C_{PD} is used to determine the dynamic power consumption, per multiplexer.
5. $P_D = V_{CC}^2 f_i (C_{PD} + C_L)$ where f_i = Input Frequency, C_L = Output Load Capacitance, V_{CC} = Supply Voltage.

Test Circuits and Waveforms

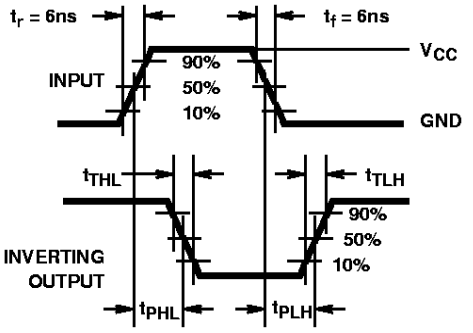


FIGURE 1. HC AND HCT TRANSITION TIMES AND PROPAGATION DELAY TIMES, COMBINATION LOGIC

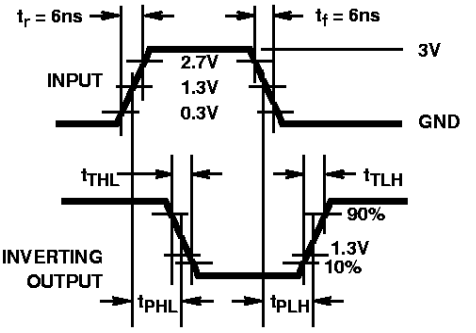


FIGURE 2. HCT TRANSITION TIMES AND PROPAGATION DELAY TIMES, COMBINATION LOGIC

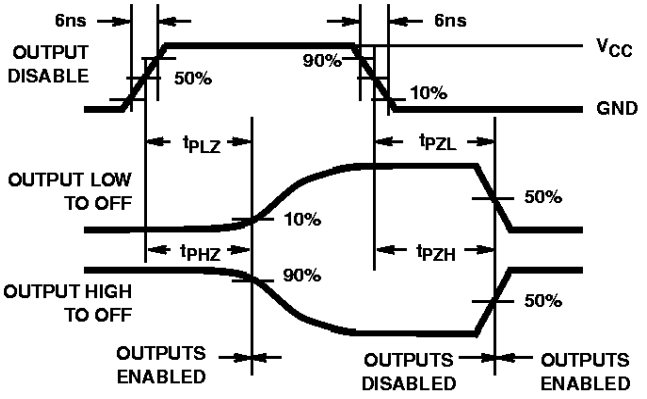


FIGURE 3. HC THREE-STATE PROPAGATION DELAY WAVEFORM

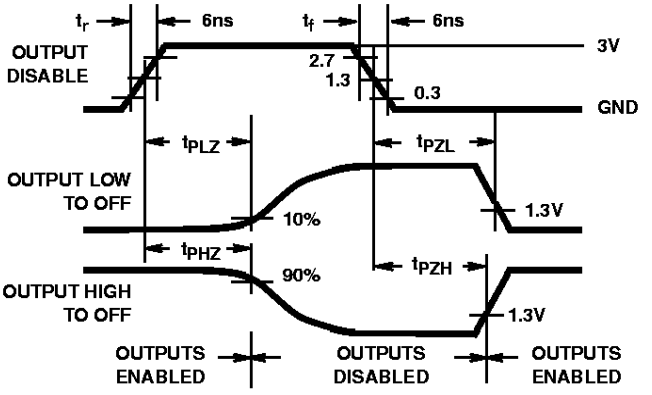
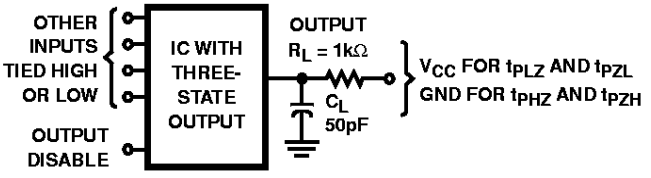


FIGURE 4. HCT THREE-STATE PROPAGATION DELAY WAVEFORM



NOTE: Open drain waveforms t_{PLZ} and t_{PZL} are the same as those for three-state shown on the left. The test circuit is Output R_L = 1kΩ to V_{CC}, C_L = 50pF.

FIGURE 5. HC AND HCT THREE-STATE PROPAGATION DELAY TEST CIRCUIT